

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

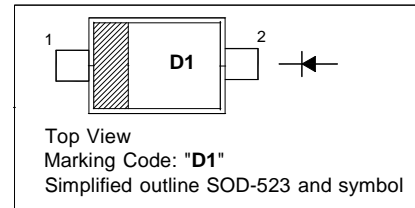
for rectifying small power applications

Features

- Ultra small mold type
- Low forward voltage
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

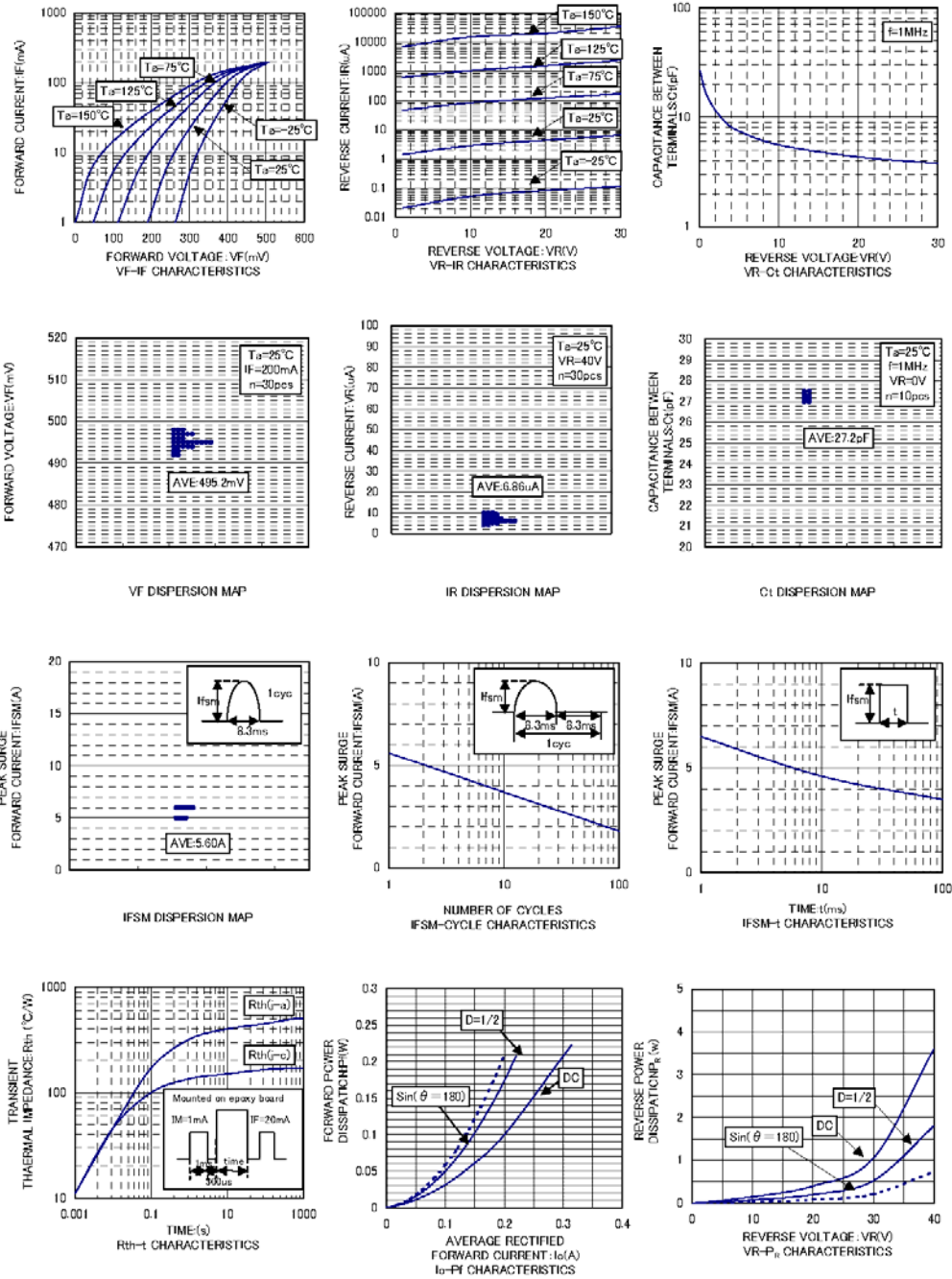


Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RM}	45	V
Reverse Voltage	V _R	40	V
Mean Rectifying Current	I _O	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I _{FSM}	1	A
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

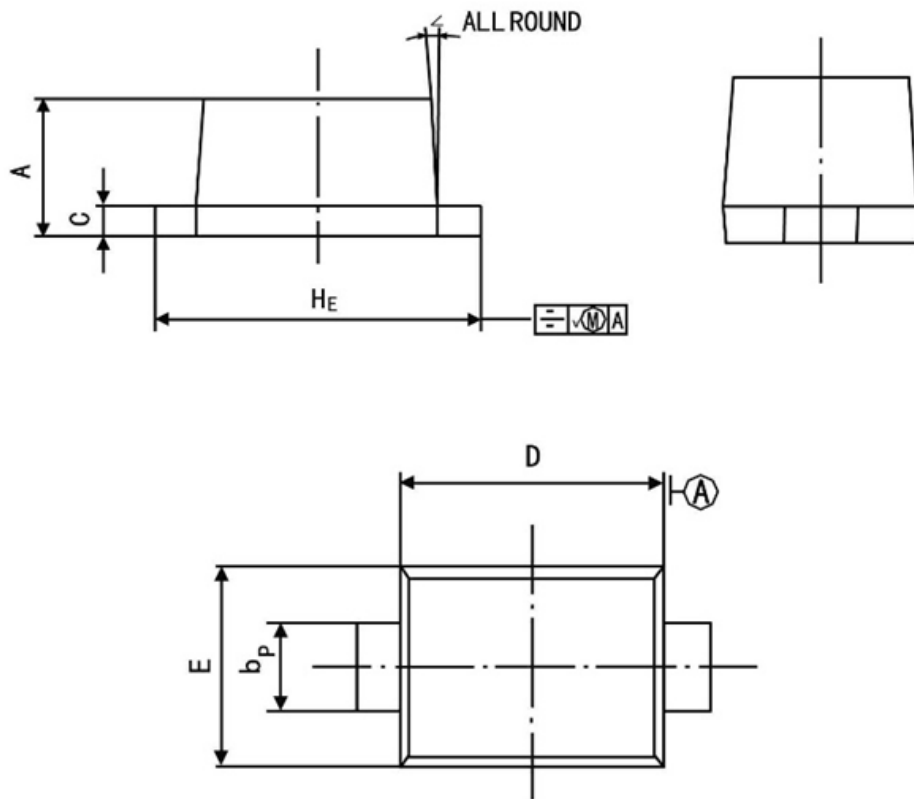
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 10 mA at I _F = 100 mA at I _F = 200 mA	V _F	0.16 0.31 0.41	0.3 0.45 0.54	V
Reverse Current at V _R = 10 V at V _R = 40 V	I _R	- -	20 90	μA



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
bp	0.30	0.40
C	0.100	0.14
D	1.15	1.25
E	0.75	0.85
HE	1.50	1.70
V	—	0.10
∠	—	5°